

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(channel) and (substrate or wafer) and (gate near dielectric) and (gate near stack) and (mask or photoresist or resist) and (gate near mandrel) and (remov\$3 or pattern\$3 or etch\$3) and (fill\$3) and (spacer or sidewall or side near wall or side-wall).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:26
L2	67113	(channel) near (region or area)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:27
L3	17715	(gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:27
L4	19	(gate near mandrel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:27
L5	6715	2 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:27
L6	3	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:27
L7	1142392	(spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:28
L8	3	6 and 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:28
L9	98518	(source or drain) near (region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:28

L10	3	8 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:28
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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	(gate near mandrel) same (spacer or side near wall or side-wall or sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:19
L2	7	(gate near mandrel) and (spacer or side near wall or side-wall or sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:20
L3	61	(gate near3 mandrel) and (spacer or side near wall or side-wall or sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:19
L4	1142392	(spacer or side near wall or side-wall or sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:20
L5	114	(gate near3 mandrel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:20
L6	61	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:20
L7	46	6 and (gate neat mandrel) with (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:30
L8	50	6 and (gate neat mandrel) same (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:30
L9	39	(7 or 8) and (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:22

L10	12	9 and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:22
L11	2	6 and (gate near mandrel) with (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:30
L12	6	6 and (gate near mandrel) same (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:30
L13	61	6 and (gate near3 mandrel) and (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:31
L14	19	6 and (gate near3 mandrel) with (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:31
L15	7	6 and (gate near mandrel) and (spacer or sidewall or side-wall or side near wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:31